



#### REVISION HISTORY

<u>Revision</u>	<u>Description</u>	<u>Issue Date</u>
Rev. 1.0	Initial Issue	Aug.1.2007
Rev. 1.1	Revised $V_{IH}$ to TTL compatible	Jan.9.2008
Rev. 1.2	Revised $I_{DR}$ (TYP.)	Feb.22.2008
Rev. 1.3	Revised $V_{IH}$ to $0.7 \cdot V_{CC}$	May.6.2008
Rev. 1.4	Revised $V_{DR}$	Mar.3.2009
Rev. 1.5	Revised <b>FEATURES &amp; ORDERING INFORMATION</b> <b>Lead free and green package available</b> to <b>Green package available</b> Added packing type in <b>ORDERING INFORMATION</b> Deleted $T_{SOLDER}$ in <b>ABSOLUTE MAXIMUM RATINGS</b> Revised <b>PACKAGE OUTLINE DIMENSION</b> in page9/10/12/13	May.6.2010
Rev. 1.6	Revised <b>ORDERING INFORMATION</b> in page 14	Aug.30.2010
Rev. 1.7	Added SL Grade Deleted E Grade Revised $I_{SB1}/I_{DR}$	Aug.9.2011

### FEATURES

- Fast access time : 55/70ns
- Low power consumption:  
Operating current : 20/18mA (TYP.)  
Standby current : 1 $\mu$ A (TYP.)
- Single 2.7V ~ 5.5V power supply
- All outputs TTL compatible
- Fully static operation
- Tri-state output
- Data retention voltage : 1.5V (MIN.)
- **Green package available**
- Package : 32-pin 8mm x 20mm TSOP-I  
32-pin 8mm x 13.4mm STSOP  
32-pin 450 mil SOP  
32-pin 600 mil P-DIP  
36-ball 6mm x 8mm TFBGA

### GENERAL DESCRIPTION

The LY62W2568 is a 2,097,152-bit low power CMOS static random access memory organized as 262,144 words by 8 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

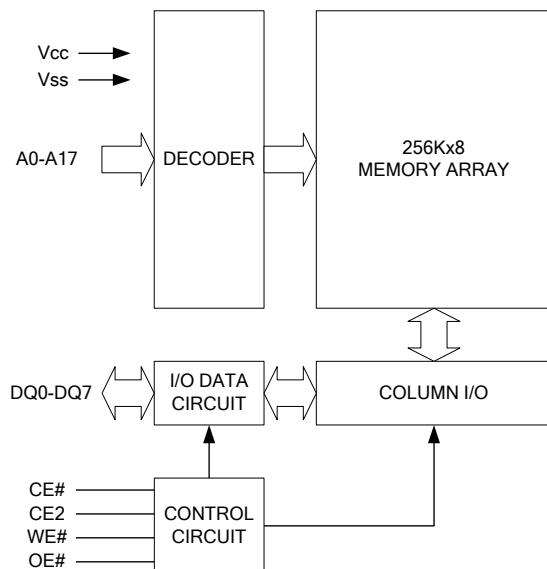
The LY62W2568 is well designed for very low power system applications, and particularly well suited for battery back-up nonvolatile memory application.

The LY62W2568 operates from a single power supply of 2.7V ~ 5.5V and all outputs are fully TTL compatible

### PRODUCT FAMILY

Product Family	Operating Temperature	Vcc Range	Speed	Power Dissipation	
				Standby(I <sub>SB1</sub> ,TYP.)	Operating(I <sub>CC</sub> ,TYP.)
LY62W2568	0 ~ 70°C	2.7 ~ 5.5V	55/70ns	1 $\mu$ A	20/18mA
LY62W2568(I)	-40 ~ 85°C	2.7 ~ 5.5V	55/70ns	1 $\mu$ A	20/18mA

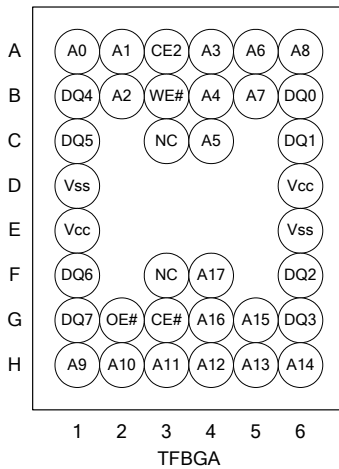
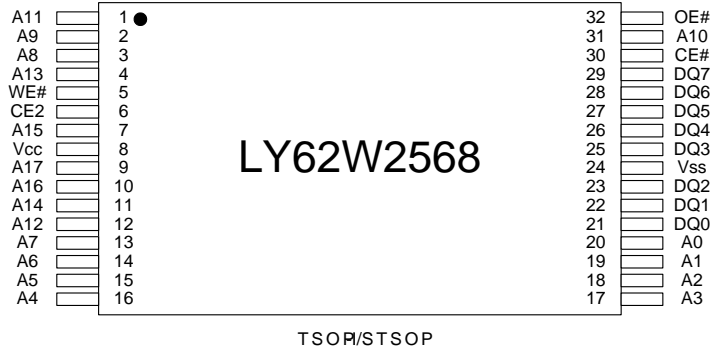
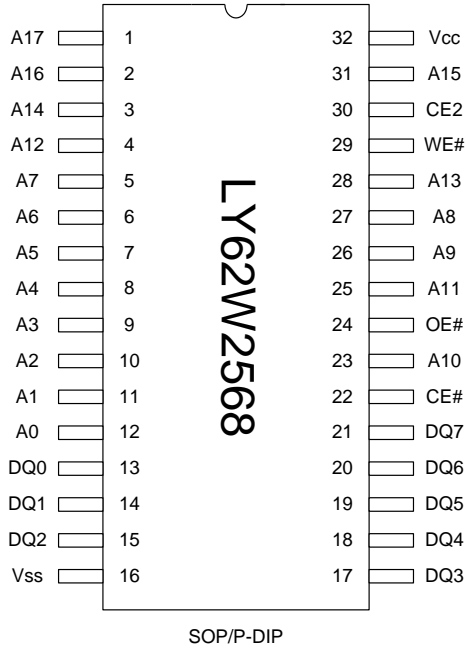
### FUNCTIONAL BLOCK DIAGRAM



### PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A17	Address Inputs
DQ0 - DQ7	Data Inputs/Outputs
CE#, CE2	Chip Enable Inputs
WE#	Write Enable Input
OE#	Output Enable Input
Vcc	Power Supply
Vss	Ground
NC	No Connection

### PIN CONFIGURATION





#### ABSOLUTE MAXIMUM RATINGS\*

PARAMETER	SYMBOL	RATING	UNIT
Voltage on Vcc relative to Vss	V <sub>T1</sub>	-0.5 to 6.5	V
Voltage on any other pin relative to Vss	V <sub>T2</sub>	-0.5 to V <sub>cc</sub> +0.5	V
Operating Temperature	T <sub>A</sub>	0 to 70(C grade)	°C
		-40 to 85(I grade)	
Storage Temperature	T <sub>STG</sub>	-65 to 150	°C
Power Dissipation	P <sub>D</sub>	1	W
DC Output Current	I <sub>OUT</sub>	50	mA

\*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

#### TRUTH TABLE

MODE	CE#	CE2	OE#	WE#	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	X	High-Z	I <sub>SB1</sub>
	X	L	X	X	High-Z	I <sub>SB1</sub>
Output Disable	L	H	H	H	High-Z	I <sub>cc</sub> , I <sub>cc1</sub>
Read	L	H	L	H	D <sub>OUT</sub>	I <sub>cc</sub> , I <sub>cc1</sub>
Write	L	H	X	L	D <sub>IN</sub>	I <sub>cc</sub> , I <sub>cc1</sub>

Note: H = V<sub>IH</sub>, L = V<sub>IL</sub>, X = Don't care.

**DC ELECTRICAL CHARACTERISTICS**

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP. <sup>4</sup>	MAX.	UNIT		
Supply Voltage	V <sub>CC</sub>		2.7	3.0	5.5	V		
Input High Voltage	V <sub>IH</sub> <sup>1</sup>		0.7*V <sub>CC</sub>	-	V <sub>CC</sub> +0.3	V		
Input Low Voltage	V <sub>IL</sub> <sup>2</sup>		- 0.2	-	0.6	V		
Input Leakage Current	I <sub>LI</sub>	V <sub>CC</sub> ≥ V <sub>IN</sub> ≥ V <sub>SS</sub>	- 1	-	1	μA		
Output Leakage Current	I <sub>LO</sub>	V <sub>CC</sub> ≥ V <sub>OUT</sub> ≥ V <sub>SS</sub> , Output Disabled	- 1	-	1	μA		
Output High Voltage	V <sub>OH</sub>	I <sub>OH</sub> = -1mA	2.4	2.7	-	V		
Output Low Voltage	V <sub>OL</sub>	I <sub>OL</sub> = 2mA	-	-	0.4	V		
Average Operating Power supply Current	I <sub>CC</sub>	Cycle time = Min. CE# = V <sub>IL</sub> and CE2 = V <sub>IH</sub> , I <sub>I/O</sub> = 0mA Other pins at V <sub>IL</sub> or V <sub>IH</sub>	- 55	-	20	60	mA	
			- 70	-	18	50	mA	
	I <sub>CC1</sub>	Cycle time = 1μs CE# = 0.2V and CE2 ≥ V <sub>CC</sub> -0.2V, I <sub>I/O</sub> = 0mA Other pins at 0.2V or V <sub>CC</sub> - 0.2V	-	4	10	mA		
Standby Power Supply Current	I <sub>SB1</sub>	CE# ≥ V <sub>CC</sub> -0.2V or CE2 ≤ 0.2V Others at 0.2V or V <sub>CC</sub> - 0.2V	LL/LLI	-	1	50	μA	
			SL <sup>*5</sup>	25°C	-	1	5	μA
			SLI <sup>*5</sup>	40°C	-	1	5	μA
			SL	-	1	20	μA	
			SLI	-	1	25	μA	

Notes:

- V<sub>IH</sub>(max) = V<sub>CC</sub> + 3.0V for pulse width less than 10ns.
- V<sub>IL</sub>(min) = V<sub>SS</sub> - 3.0V for pulse width less than 10ns.
- Over/Undershoot specifications are characterized, not 100% tested.
- Typical values are included for reference only and are not guaranteed or tested.  
Typical values are measured at V<sub>CC</sub> = V<sub>CC</sub>(TYP.) and T<sub>A</sub> = 25°C
- This parameter is measured at V<sub>CC</sub> = 3.0V

**CAPACITANCE (T<sub>A</sub> = 25°C, f = 1.0MHz)**

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	C <sub>IN</sub>	-	6	pF
Input/Output Capacitance	C <sub>I/O</sub>	-	8	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

**AC TEST CONDITIONS**

Input Pulse Levels	0.2V to V <sub>CC</sub> - 0.2V
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	1.5V
Output Load	C <sub>L</sub> = 30pF + 1TTL, I <sub>OH</sub> /I <sub>OL</sub> = -2mA/4mA



### AC ELECTRICAL CHARACTERISTICS

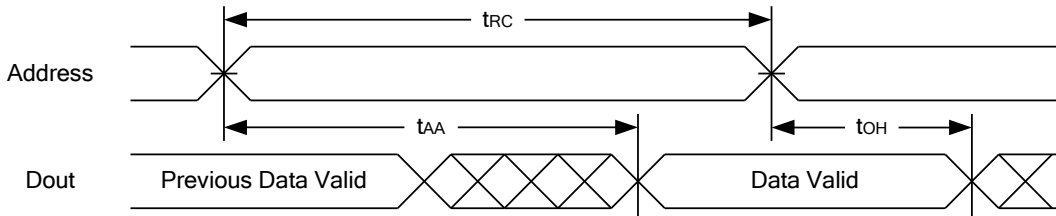
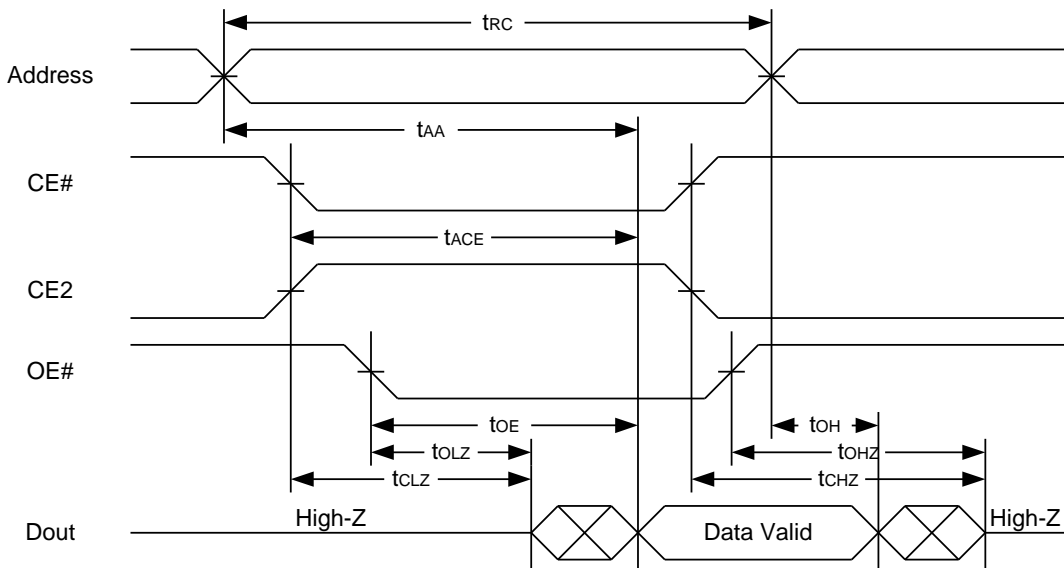
#### (1) READ CYCLE

PARAMETER	SYM.	LY62W2568-55		LY62W2568-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t <sub>RC</sub>	55	-	70	-	ns
Address Access Time	t <sub>AA</sub>	-	55	-	70	ns
Chip Enable Access Time	t <sub>ACE</sub>	-	55	-	70	ns
Output Enable Access Time	t <sub>OE</sub>	-	30	-	35	ns
Chip Enable to Output in Low-Z	t <sub>CLZ</sub> *	10	-	10	-	ns
Output Enable to Output in Low-Z	t <sub>OLZ</sub> *	5	-	5	-	ns
Chip Disable to Output in High-Z	t <sub>CHZ</sub> *	-	20	-	25	ns
Output Disable to Output in High-Z	t <sub>OHZ</sub> *	-	20	-	25	ns
Output Hold from Address Change	t <sub>OH</sub>	10	-	10	-	ns

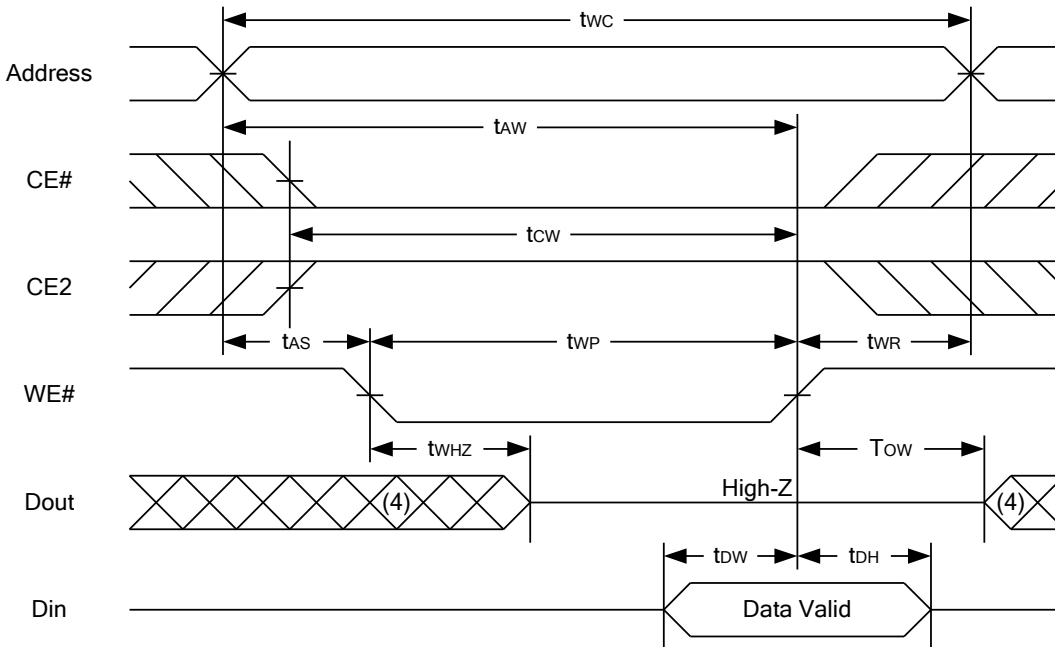
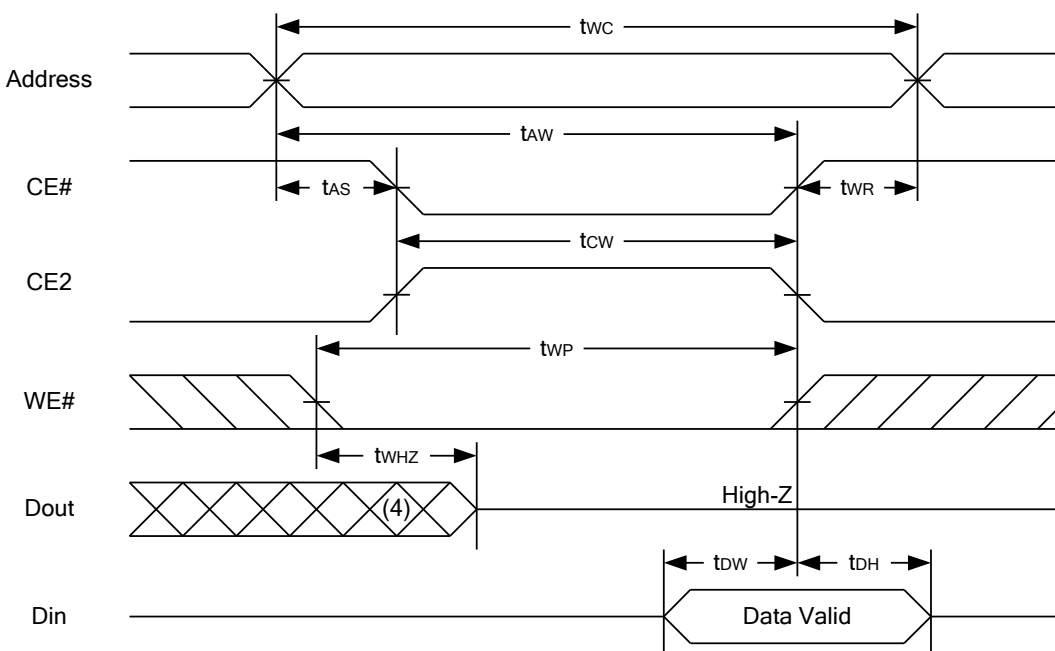
#### (2) WRITE CYCLE

PARAMETER	SYM.	LY62W2568-55		LY62W2568-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t <sub>WC</sub>	55	-	70	-	ns
Address Valid to End of Write	t <sub>AW</sub>	50	-	60	-	ns
Chip Enable to End of Write	t <sub>CW</sub>	50	-	60	-	ns
Address Set-up Time	t <sub>AS</sub>	0	-	0	-	ns
Write Pulse Width	t <sub>WP</sub>	45	-	55	-	ns
Write Recovery Time	t <sub>WR</sub>	0	-	0	-	ns
Data to Write Time Overlap	t <sub>DW</sub>	25	-	30	-	ns
Data Hold from End of Write Time	t <sub>DH</sub>	0	-	0	-	ns
Output Active from End of Write	t <sub>OW</sub> *	5	-	5	-	ns
Write to Output in High-Z	t <sub>WHZ</sub> *	-	20	-	25	ns

\*These parameters are guaranteed by device characterization, but not production tested.

**TIMING WAVEFORMS**
**READ CYCLE 1 (Address Controlled) (1,2)**

**READ CYCLE 2 (CE# and CE2 and OE# Controlled) (1,3,4,5)**

**Notes :**

1. WE# is high for read cycle.
2. Device is continuously selected OE# = low, CE# = low., CE2 = high.
3. Address must be valid prior to or coincident with CE# = low, CE2 = high; otherwise  $t_{AA}$  is the limiting parameter.
4.  $t_{CLZ}$ ,  $t_{OLZ}$ ,  $t_{CHZ}$  and  $t_{OHZ}$  are specified with  $C_L = 5\text{pF}$ . Transition is measured  $\pm 500\text{mV}$  from steady state.
5. At any given temperature and voltage condition,  $t_{CHZ}$  is less than  $t_{CLZ}$ ,  $t_{OHZ}$  is less than  $t_{OLZ}$ .

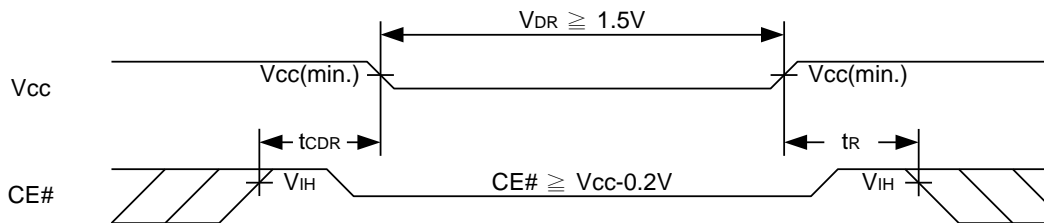
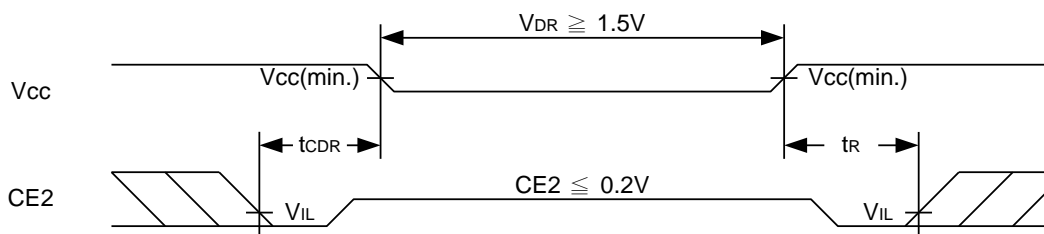
**WRITE CYCLE 1 (WE# Controlled) (1,2,3,5,6)**

**WRITE CYCLE 2 (CE# and CE2 Controlled) (1,2,5,6)**

**Notes :**

1. WE#, CE# must be high or CE2 must be low during all address transitions.
2. A write occurs during the overlap of a low CE#, high CE2, low WE#.
3. During a WE#-controlled write cycle with OE# low,  $t_{wp}$  must be greater than  $t_{whz} + t_{dw}$  to allow the drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the CE# low transition and CE2 high transition occurs simultaneously with or after WE# low transition, the outputs remain in a high impedance state.
6.  $t_{ow}$  and  $t_{whz}$  are specified with  $C_L = 5pF$ . Transition is measured  $\pm 500mV$  from steady state.

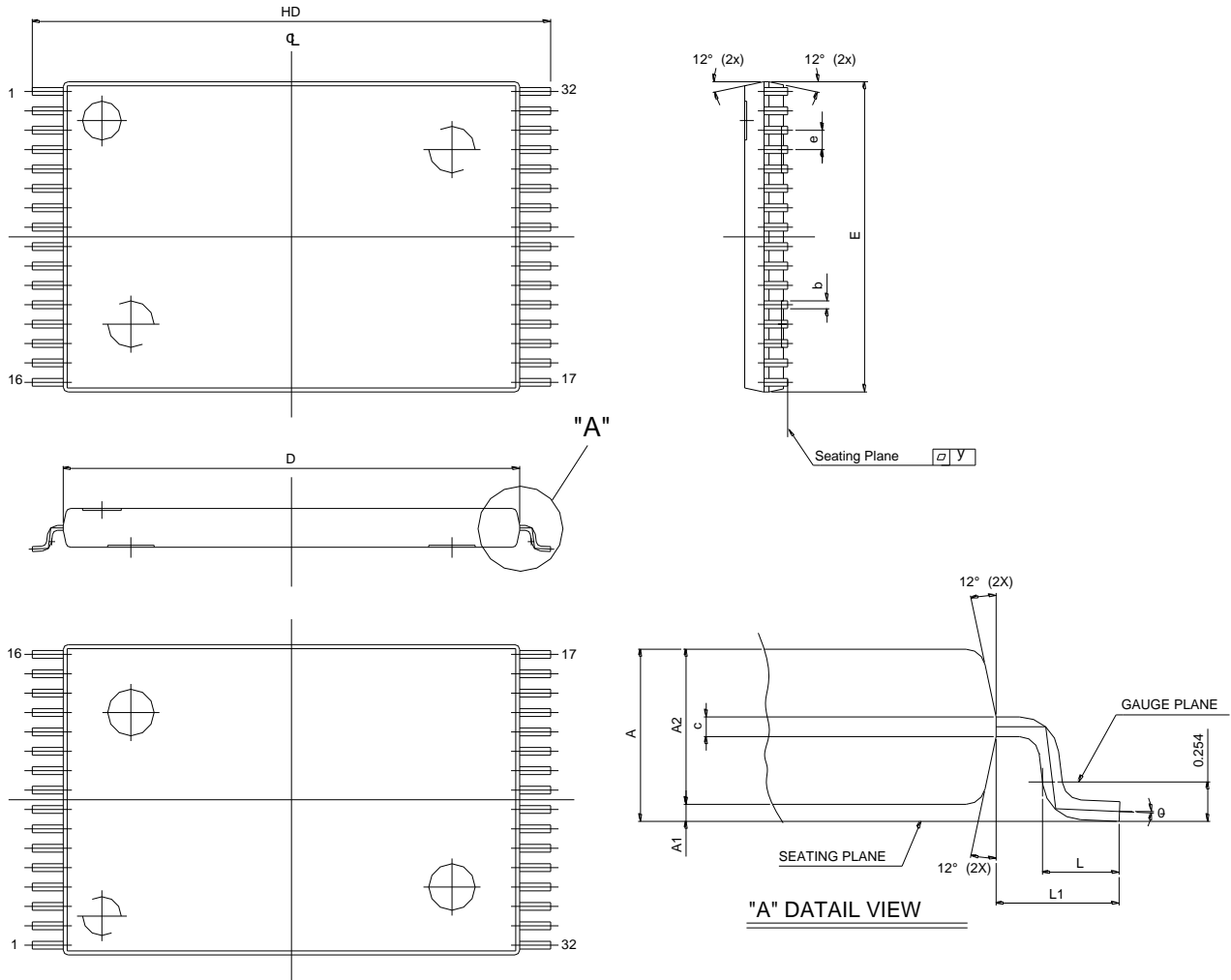
**DATA RETENTION CHARACTERISTICS**

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
V <sub>CC</sub> for Data Retention	V <sub>DR</sub>	CE# ≥ V <sub>CC</sub> - 0.2V or CE2 ≤ 0.2V	1.5	-	5.5	V	
Data Retention Current	I <sub>DR</sub>	V <sub>CC</sub> = 1.5V CE# ≥ V <sub>CC</sub> - 0.2V or CE2 ≤ 0.2V	LL/LLI	-	0.5	20	μA
			SL 25°C	-	0.5	4	μA
		SLI 40°C	-	0.5	4	μA	
		Other pins at 0.2V or V <sub>CC</sub> -0.2V	SL/SLI	-	0.5	15	μA
Chip Disable to Data Retention Time	t <sub>CDR</sub>	See Data Retention Waveforms (below)	0	-	-	ns	
Recovery Time	t <sub>R</sub>		t <sub>RC</sub> *	-	-	ns	

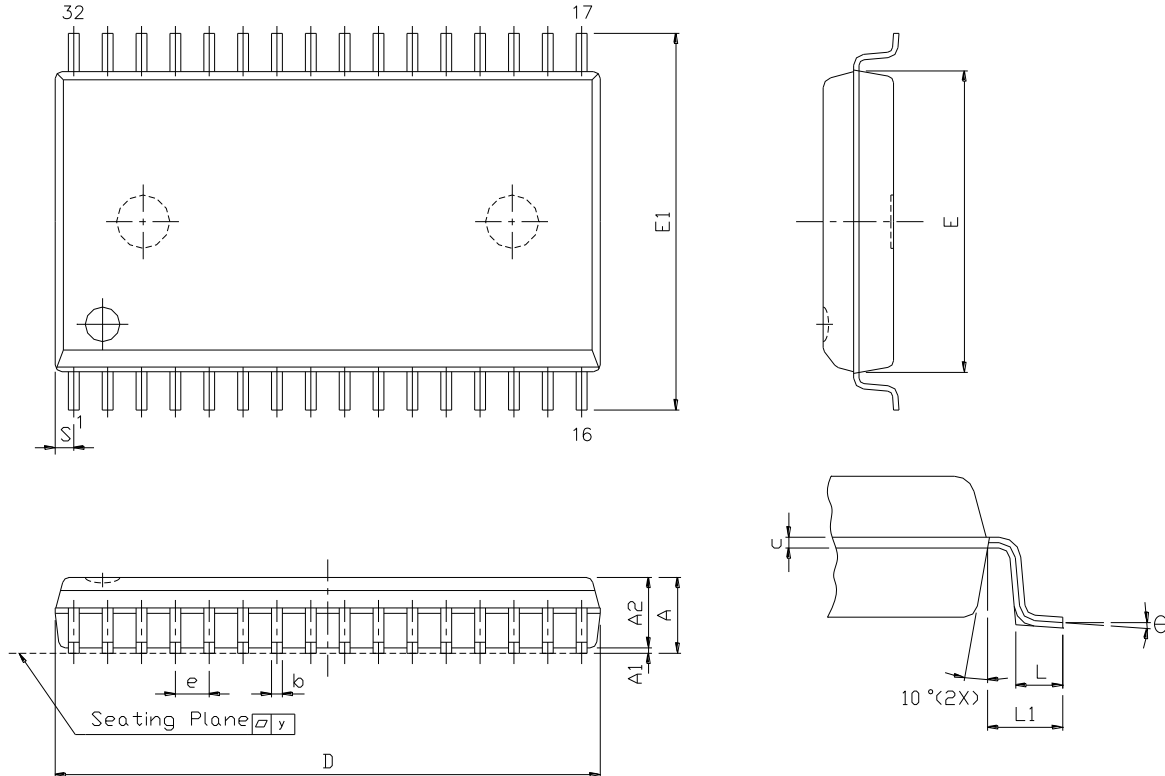
 t<sub>RC</sub>\* = Read Cycle Time

**DATA RETENTION WAVEFORM**
**Low V<sub>CC</sub> Data Retention Waveform (1) (CE# controlled)**

**Low V<sub>CC</sub> Data Retention Waveform (2) (CE2 controlled)**


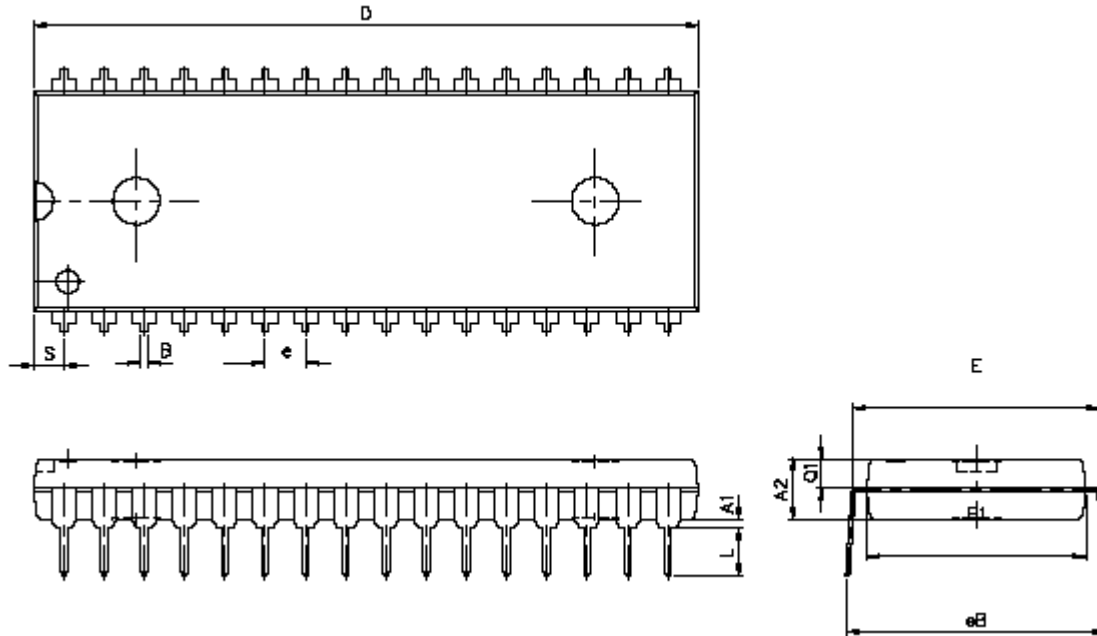


**32 pin 8mm x 13.4mm STSOP Package Outline Dimension**


SYM.	UNIT	INCH(BASE)	MM(REF)
A		0.049 (MAX)	1.25 (MAX)
A1		0.004 ±0.002	0.10 ±0.05
A2		0.039 ±0.002	1.00 ±0.05
b		0.009 ±0.002	0.22 ±0.05
c		0.006 ±0.002	0.155 ±0.055
D		0.465 ±0.008	11.80 ±0.20
E		0.315 ±0.008	8.00 ±0.20
e		0.020 (TYP)	0.50 (TYP)
HD		0.528±0.008	13.40 ±0.20.
L		0.02 ±0.008	0.50 ±0.20
L1		0.031 ±0.005	0.8 ±0.125
y		0.003 (MAX)	0.076 (MAX)
Θ		0°~5°	0°~5°

**32 pin 450 mil SOP Package Outline Dimension**


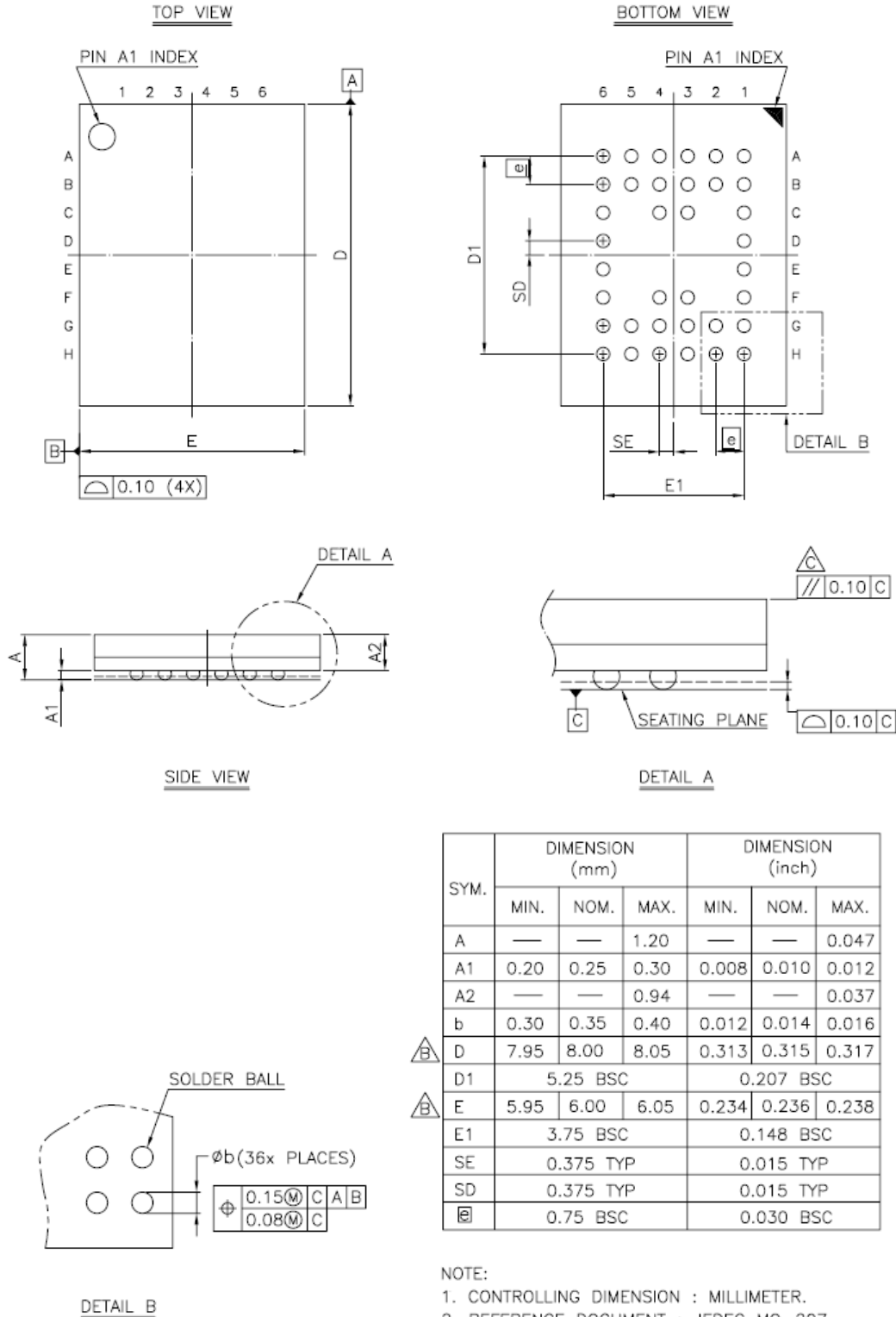
SYM.	UNIT	
	INCH.(BASE)	MM(REF)
A	0.120(MAX)	3.048(MAX)
A1	0.004(MIN)	0.102(MIN)
A2	0.116(MAX)	2.946(MAX)
b	0.016(TYP)	0.406(TYP)
c	0.008(TYP)	0.203(TYP)
D	0.817(MAX)	20.75(MAX)
E	0.445±0.006	11.303±0.152
E1	0.555±0.025	14.097±0.635
e	0.050(TYP)	1.270(TYP)
L	0.033±0.017	0.838±0.432
L1	0.055±0.008	1.397±0.203
S	0.026(MAX)	0.660(MAX)
y	0.004(MAX)	0.101(MAX)
Θ	0° -10°	0° -10°

**32 pin 600 mil P-DIP Package Outline Dimension**


SYM.	UNIT	INCH(BASE)	MM(REF)
A1		0.015(MIN)	0.381(MIN)
A2		0.155±0.005	3.937±0.127
B		0.018±0.005	0.457±0.127
D		1.650±0.01	41.910±0.254
E		0.600±0.010	15.240±0.254
E1		0.545±0.005	13.843±0.127
e		0.100(TYP)	2.540(TYP)
eB		0.650±0.020	16.510±0.508.
L		0.158±0.043	4.013±1.092
S		0.075±0.010	1.905±0.254
Q1		0.070±0.005	1.778±0.127

Note : D/E1/S dimension do not include mold flash.

### 36 ball 6mm x 8mm TFBGA Package Outline Dimension



NOTE:  
 1. CONTROLLING DIMENSION : MILLIMETER.  
 2. REFERENCE DOCUMENT : JEDEC MO-207.



### ORDERING INFORMATION

LY62W2568 U V - WW XX Y Z

**Z** : Packing Type

Blank : Tube or Tray
Tube : 32-pin 450 mil SOP
32-pin 600 mil P-DIP
Tray : 32-pin 8 mm x 20 mm TSOP-I
32-pin 8 mm x 13.4 mm STSOP
36-ball 6 mm x 8 mm TFBGA
T : Tape Reel

**Y** : Temperature Range

Blank : (Commercial) 0°C ~ 70°C
I : (Industrial) -40°C ~ +85°C

**XX** : Power Type

LL : Ultra Low Power
SL : Special Ultra Low Power

**WW** : Access Time(Speed)

**V** : Lead Information

L : Green Package
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**U** : Package Type

S : 32-pin 450 mil SOP
P : 32-pin 600 mil P-DIP
L : 32-pin 8 mm x 20 mm TSOP-I
R : 32-pin 8 mm x 13.4 mm STSOP
G : 36-ball 6 mm x 8 mm TFBGA



**Lyontek Inc.**

**LY62W2568**

Rev. 1.7

**256K X 8 BIT LOW POWER CMOS SRAM**

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